

C3D10065ISilicon Carbide Schottky Diode

Z-REC™ RECTIFIER

 \mathbf{V}_{RRM} = 650 V $\mathbf{I}_{F}(\mathbf{T}_{c}=\mathbf{125}^{\circ}\mathbf{C}) = 10 \text{ A}$ \mathbf{Q}_{c} = 25 nC

Features

- 650-Volt Schottky Rectifier
- Ceramic Package provides 2.5kV isolation
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V_F

Benefits

- Electrically Isolated Package
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

PIN 1 O

Package

Applications

- HVAC
- Switch Mode Power Supplies

Part Number	Package	Marking
C3D10065I	Isolated TO-220-2	C3D10065I

Halogen-Free

Maximum Ratings ($T_c = 25$ °C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	650	V		
V _{RSM}	Surge Peak Reverse Voltage	650	V		
V _{DC}	DC Blocking Voltage	650	V		
I _F	Continuous Forward Current	19 10 8.5	А	T _c =25°C T _c =125°C T _c =135°C	
I _{FRM}	Repetitive Peak Forward Surge Current	28.6 17.7	А	T_c =25°C, t_p =10 ms, Half Sine pulse T_c =110°C, t_p =10 ms, Half Sine pulse	
I _{FSM}	Non-Repetitive Peak Forward Surge Current	80 70	А	T_c =25°C, t_p =10 ms, Half Sine pulse T_c =110°C, t_p =10 ms, Half Sine pulse	
P _{tot}	Power Dissipation	60 26	W	T _c =25°C T _c =110°C	
Т,	Operating Junction Range	-55 to +175	°C		
T_{stg},T_{c}	Storage Temperature and Case Temperature	-55 to +150	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



Electrical Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 2.0	1.8 2.4	V	I _F = 10 A T _J =25°C I _F = 10 A T _J =175°C	
I_R	Reverse Current	12 24	60 220	μA	$V_R = 650 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 650 \text{ V } T_J = 175^{\circ}\text{C}$	
Q _c	Total Capacitive Charge	25		nC	$V_R = 650 \text{ V, } I_F = 10 \text{ A}$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	
С	Total Capacitance	480 50 42		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	

Note:

Thermal Characteristics

Symbol	Parameter	Тур.	Unit
$R_{\theta JC}$	Package Thermal Resistance from Junction to Case	2.6	°C/W

Typical Performance

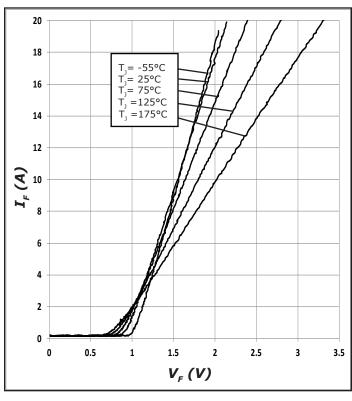


Figure 1. Forward Characteristics

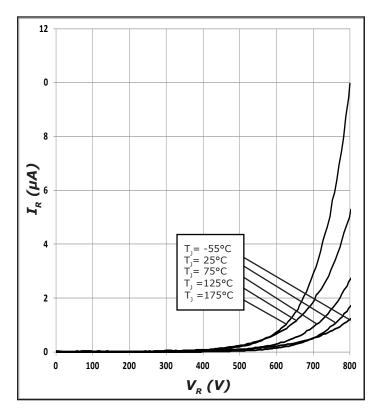
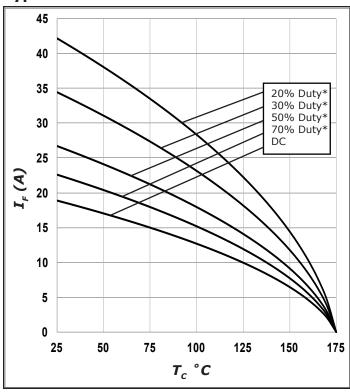


Figure 2. Reverse Characteristics

^{1.} This is a majority carrier diode, so there is no reverse recovery charge.



Typical Performance



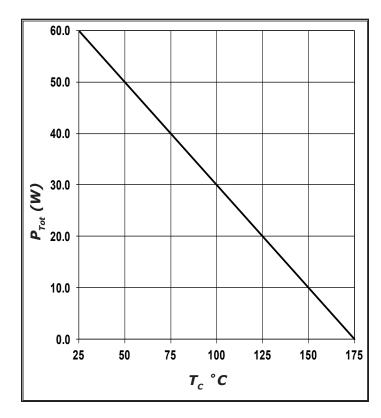


Figure 3. Current Derating

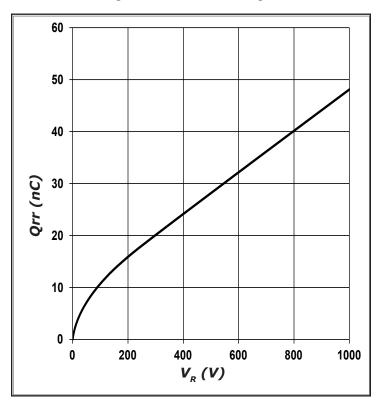


Figure 5. Recovery Charge vs. Reverse Voltage

Figure 4. Power Derating

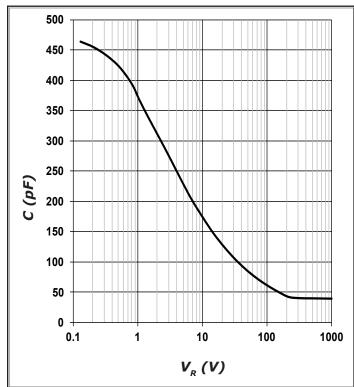


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

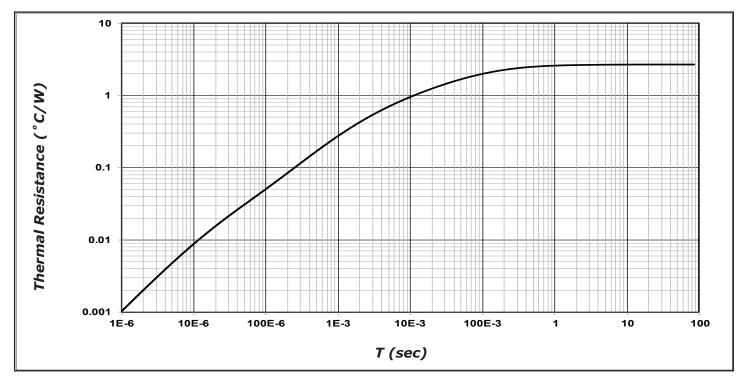


Figure 7. Transient Thermal Impedance

Diode Model

$$Vf_T = V_T + If^*R_T$$

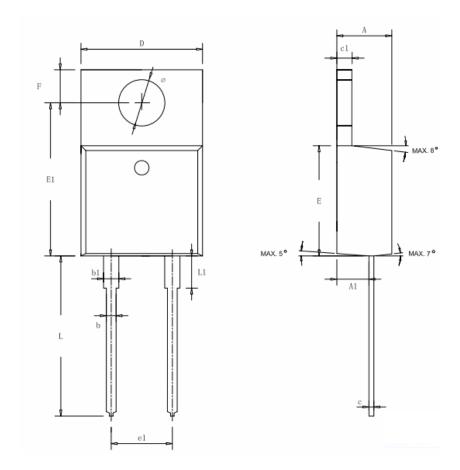
$$V_T = 0.98 + (T_J^* - 1.6^*10^{-3})$$

$$R_T = 0.04 + (T_J^* 0.522^*10^{-3})$$

Note: T_i = Diode Junction Temperature In Degrees Celsius



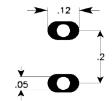
Package Dimensions



	Dimensions i	n Millimeters	eters Dimensions in Inches		
Symbol	Min	Max	Min	Max	
Α	4.420	4.720	1.174	0.186	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.360	0.460	0.014	0.018	
c1	1.170	1.370	0.046	0.054	
D	9.950	10.250	0.392	0.404	
E	8.930	9.290	0.352	0.366	
E1	12.550	12.850	0.494	0.506	
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
L	13.080	13.480	0.515	0.531	
L1	2.470	2.870	0.097	0.113	
ф	3.790	3.890	0.149	0.153	



Recommended Solder Pad Layout



Measurements shown in inches TO-220-2

Part Number	Package	Marking
C3D10065I	Isolated TO-220-2	C3D10065I

Note: Recommended soldering profiles can be found in the applications note here: http://www.cree.com/power_app_notes/soldering



Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into
the human body nor in applications in which failure of the product could lead to death, personal injury or property
damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines,
cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control
systems, air traffic control systems, or weapons systems.

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